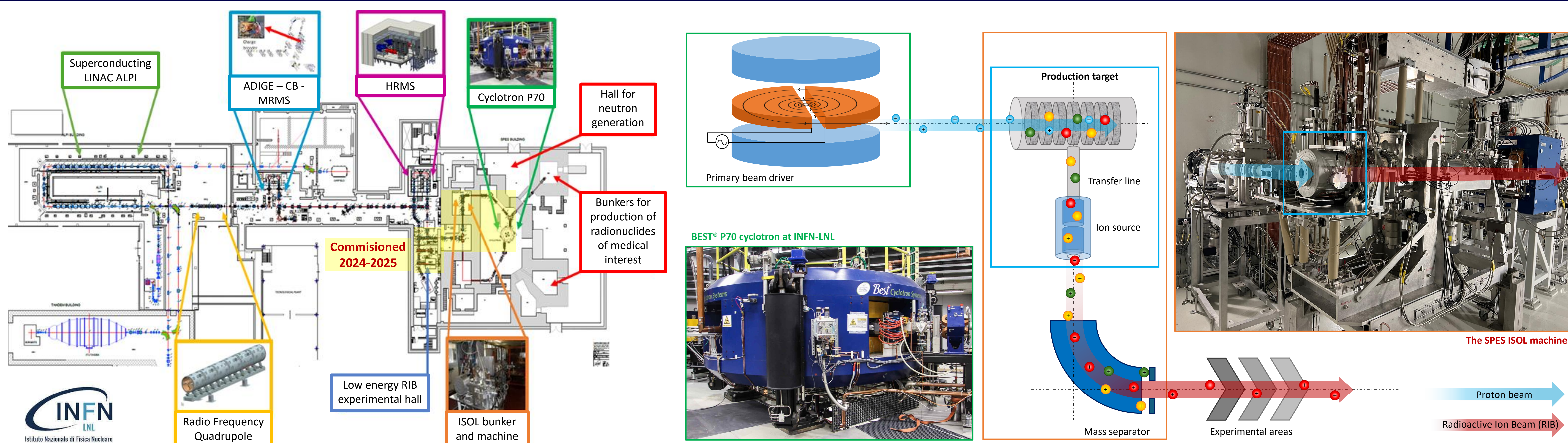


M. Ballan¹, M. L. Allegrini¹, A. Andrichetto¹, L. Antoniazzi¹, P. Antonini¹, F. Azaiez¹, L. Bellan¹, D. Benini¹, D. Bortolato¹, L. Centofante¹, S. Corradetti¹, L. De Ruvo¹, E. Fagotti¹, F. Grespan¹, G. Keppel¹, O. S. Khwairakpam¹, G. Lilli¹, M. Maggiore¹, M. Manzolaro¹, T. Marchi¹, A. Monetti¹, M. Montis¹, L. Mou¹, G. Pupillo¹, C. Roncolato¹, M. Rossignoli¹, L. Sarchiapone¹, D. Scarpa¹, G. Voltan¹

¹INFN – Legnaro National Laboratories, Legnaro, Padua, Italy,

The SPES-ISOL facility



The Target-Ion Source system

Silicon Carbide (SiC) target

Hexoloy® SiC SA:

- Commercial high-performance Silicon Carbide crafted by SAINT-GOBAIN
- High density:**
 - Good for **thermal and mechanical properties**
 - Not optimal for **isotope release** (low diffusion rates)
- Fully characterized for relevant **mechanical and thermal properties** [1]

